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P1 98.2

N-CHANNEL POWER MOS FET ARRAY SWITCHING TYPE

DESCRIPTION

The μ PA1524 is N-channel Power MOS FET Array that built in 4 circuits designed for solenoid, motor and lamp driver.

FEATURES

- 4 V driving is possible
- Large Current and Low On-state Resistance
 - $I_{D(pulse)} = \pm 6$ A
 - $R_{DS(on)} \leq 0.6 \Omega$ TYP. ($V_{GS} = 10$ V)
 - $R_{DS(on)} \leq 0.8 \Omega$ TYP. ($V_{GS} = 4$ V)
- 2.54 mm Pitch (0.1 inch)

ORDERING INFORMATION

Part Number	Package	Quality Grade
μ PA1524H	10-Pin SIP	Standard

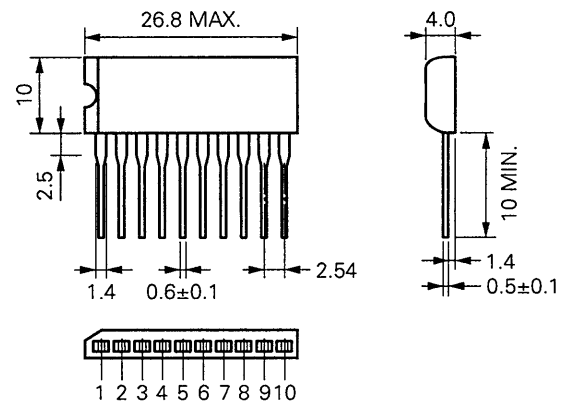
Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Drain to Source Voltage	V_{DSS}	80	V
Gate to Source Voltage	$V_{GSS(AC)}$	± 20	V
Drain Current (DC)	$I_{D(DC)}$	± 2.0	A/unit
Drain Current (pulse)	$I_{D(pulse)*}$	± 6.0	A/unit
Total Power Dissipation (4 circuits)	P_{T1}	28	W
$\langle T_c = 25^\circ\text{C} \rangle$			
Total Power Dissipation (4 circuits)	P_{T2}	3.5	W
$\langle T_a = 25^\circ\text{C} \rangle$			
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 300 \mu\text{s}$, Duty Cycle $\leq 10\%$

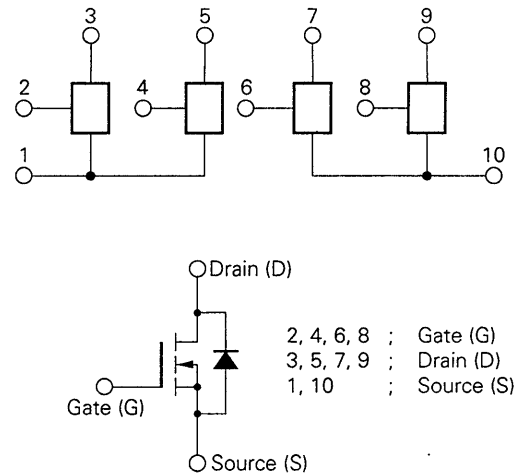
PACKAGE DIMENSIONS (in millimeters)



ELECTRODE CONNECTION

2, 4, 6, 8	GATE
3, 5, 7, 9	DRAIN
1, 10	SOURCE

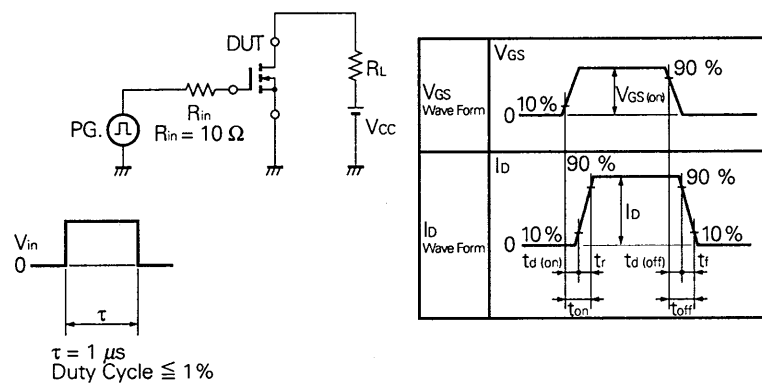
PIN CONNECTION



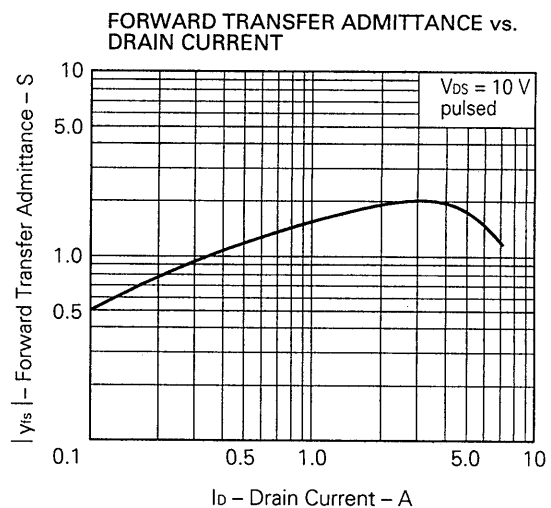
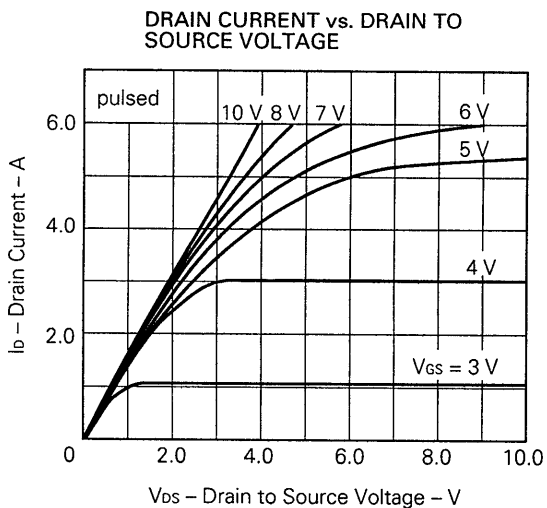
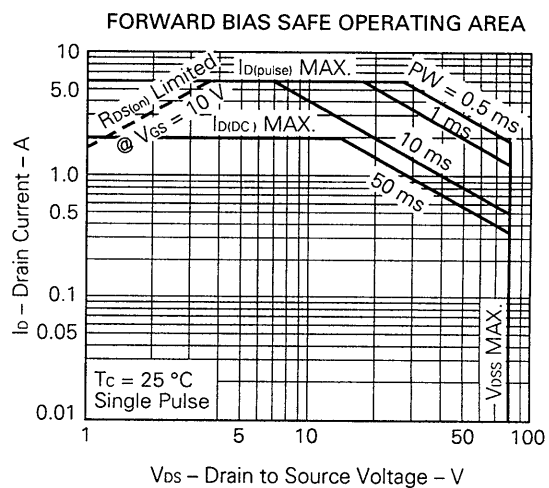
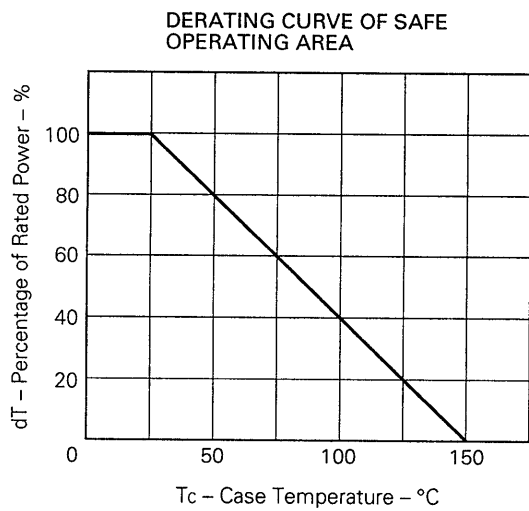
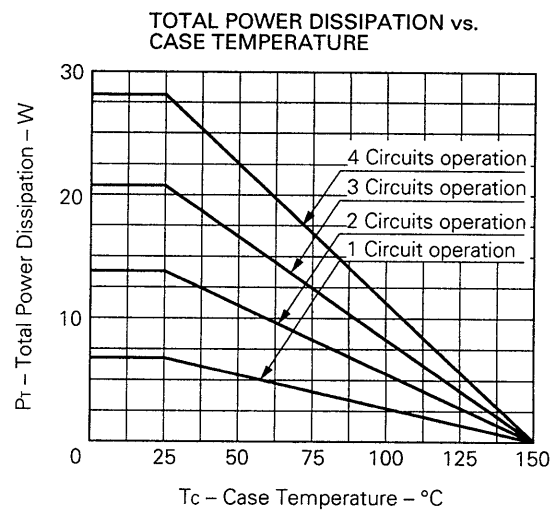
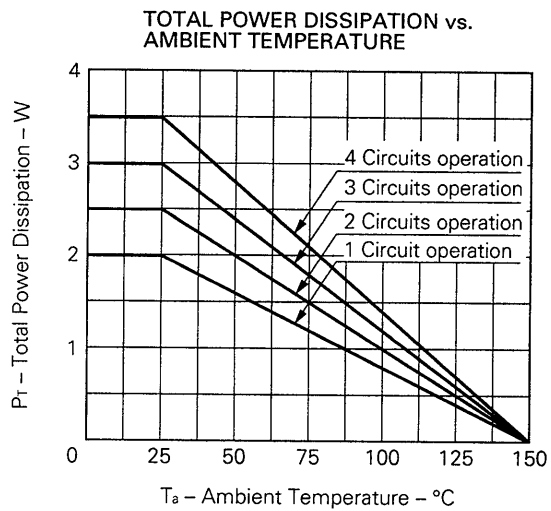
ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain Leakage Current	I _{DSS}			10	μA	V _{DS} = 80 V, V _{GS} = 0
Gate to Source Leakage Current	I _{GSS}			±100	nA	V _{GS} = ±20 V, V _{DS} = 0
Gate to Source Cutoff Voltage	V _{GS(off)}	1.0		2.5	V	V _{DS} = 10 V, I _D = 1 mA
Forward Transfer Admittance	y _{fs}	1.0			S	V _{DS} = 10 V, I _D = 1 A
Drain to Source On-state Resistance	R _{DS(on)1}		0.6	0.8	Ω	V _{GS} = 10 V, I _D = 1 A
Drain to Source On-state Resistance	R _{DS(on)2}		0.8	1.0	Ω	V _{GS} = 4 V, I _D = 1 A
Input Capacitance	C _{iss}		200		pF	V _{DS} = 10 V V _{GS} = 0 f = 1.0 MHz
Output Capacitance	C _{oss}		70		pF	
Reverse Transfer Capacitance	C _{rss}		15		pF	
Turn-On Delay Time	t _{d(on)}		45		ns	I _D = 1 A V _{GS} = 10 V V _{CC} = 50 V R _L = 50 Ω R _{in} = 10 Ω See Fig. 1
Rise Time	t _r		40		ns	
Turn-Off Delay Time	t _{d(off)}		450		ns	
Fall Time	t _f		110		ns	

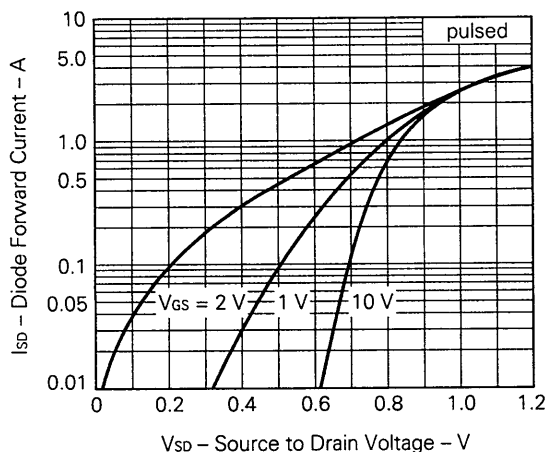
Fig. 1 Switching Test Circuit



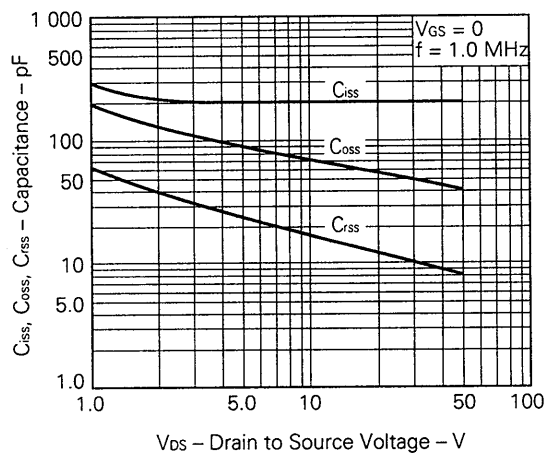
TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)



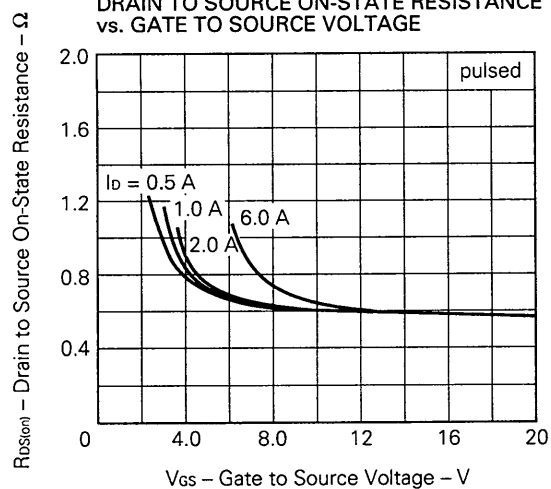
SOURCE TO DRAIN DIODE
FORWARD VOLTAGE



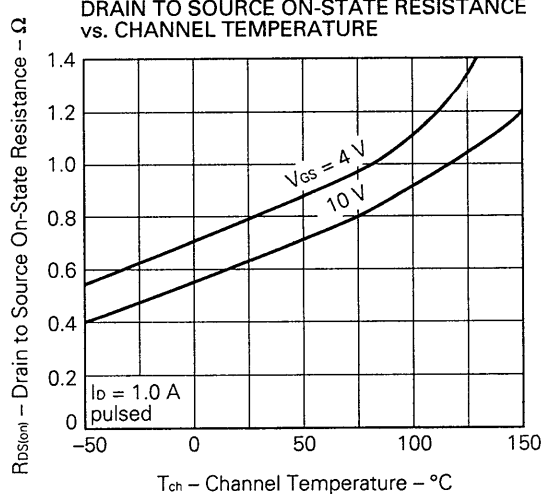
CAPACITANCE vs. DRAIN TO
SOURCE VOLTAGE



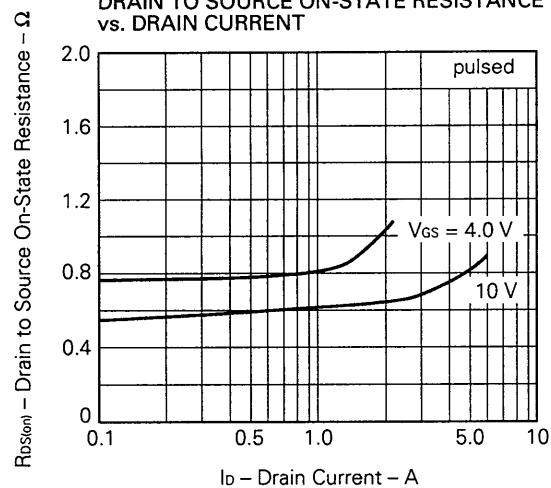
DRAIN TO SOURCE ON-STATE RESISTANCE
vs. GATE TO SOURCE VOLTAGE



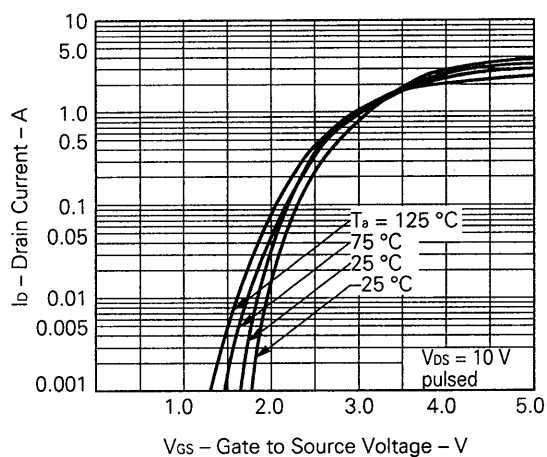
DRAIN TO SOURCE ON-STATE RESISTANCE
vs. CHANNEL TEMPERATURE



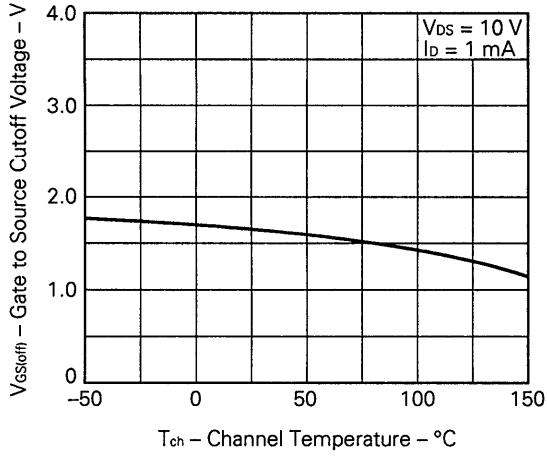
DRAIN TO SOURCE ON-STATE RESISTANCE
vs. DRAIN CURRENT



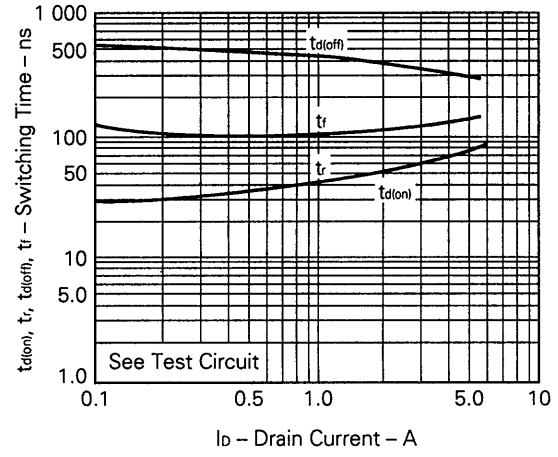
TRANSFER CHARACTERISTICS



GATE TO SOURCE CUTOFF VOLTAGE
vs. CHANNEL TEMPERATURE



SWITCHING TIME vs. DRAIN CURRENT



Reference

Application note name	No.
Quality control of NEC semiconductors devices.	TEI-1202
Quality control guide of semiconductors devices.	MEI-1202
Assembly manual of semiconductors devices.	IEI-1207
Safe operating area of Power MOS FET	TEA-1034
Application circuit using Power MOS FET	TEB-1035

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